

AMENDMENTS TO THE ABSTRACT

Please substitute the following paragraph for the abstract now appearing in the currently filed specification:

~~The present invention is provided to manufacture a~~ A method of manufacturing a semiconductor device ~~is disclosed which comprises, comprising the steps of:~~ forming a first well region by performing an ion implantation process for implanting first ions into a semiconductor substrate, and then forming a second well region in the first well region by performing an ion implantation process for implanting second ions having larger mass than the first ions; and forming a three-part or three-fold well region by performing an annealing process on the result structure wherein the lighter first ions are disposed in the upper and lower well regions and the heavier second ions are disposed in the middle well region. Therefore, it is possible to prevent TED phenomenon generated due to the high-energy heat treatment process to be performed later and to provide the increased activation ratio of ions compared to the conventional source/drain region in which only the ions having large mass are implanted by performing an annealing process after the first well region and the second well region are formed.